## AIGaAs Flip-Chip PIN Diode 100 MHz to 50 GHz

## Features

- Lower Series Resistance, $5.2 \Omega$
- Ultra Low Capacitance, 18 fF
- High Switching Cutoff Frequency, 50 GHz
- 3 Nanosecond Switching Speed
- Driven by Standard TTL
- Silicon Nitride Passivation
- Polyimide Scratch Protection


## Description

M/A-COM's MA4AGFCP910 is an Aluminum Gallium Arsenide Flip-Chip PIN diode. These devices are fabricated on OMCVD epitaxial wafers using a process designed for high device uniformity and extremely low parasitics. The diodes exhibit an extremely low RC Product, ( 0.1 ps ) and 3 nS switching characteristics.

They are fully passivated with silicon nitride and have an additional layer of a polymer for scratch protection. The protective coatings prevent damage to the junction and the anode airbridge during handling.

## Top View Shown Is With Diode Junction Up



## Package Outline

Electrical Specifications at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$

| Parameters and Test Conditions | Symbol | Units | 1 MHz \& DC <br> Specifications |  | 10 GHz Reference <br> Data $^{1,2}$ |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Total Capacitance at -5 V |  |  | Min | Typ. | Max | Min | Typ. | Max. |
| RF Resistance at +10 mA | Ct | pF |  | 0.018 | 0.021 |  | 0.018 | .021 |
| Forward Voltage at +10 mA | Rs | $\Omega$ |  |  |  |  | 5.2 | 6.0 |
| Reverse Breakdown Voltage at $10 \mathrm{uA}^{3}$ | Vf | Volts |  | 1.33 | 1.4 |  |  |  |
| Minority Carrier Lifetime | Vb | Volts | 50 | 75 |  |  |  |  |

## Notes:

1. Capacitance is determined by measuring Single Series Diode Isolation in a 50 ohm line at 10 GHz .
2. Forward Series Resistance is determined by measuring Single Series Diode Insertion Loss in a 50 ohm line at 10 GHz .
3. Reverse current will not exceed 10 microamperes at the Maximum Voltage Rating.

## Typical RF Performance



## Typical RF Performance



## Typical RF Performance



## Applications

The 20 fF capacitance of the MA4AGFCP910 allows use through mmwave switch and switched phase shifter applications. This diode is designed for use in pulsed or CW applications, where single digit nS switching speed is required. For surface mount assembly, the low capacitance of the MA4AGFCP910 makes it ideal for use in microwave multithrow switch assemblies, where the series capacitance of each "off" port adversely loads the input port and affects VSWR.
Absolute Maximum Ratings @ $25^{\circ} \mathbf{C}$

| Parameter | Maximum Ratings |
| :---: | :---: |
| Operating Temperature | $-65^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ |
| Storage Temperature | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| Junction Temperature | $+175^{\circ} \mathrm{C}$ |
| Dissipated RF \& DC Power | 50 mW |
| RF C.W. Incident Power | $+23 \mathrm{dBm} \mathrm{C.W}$. |
| Mounting Temperature | $+300^{\circ} \mathrm{C}$ for 10 seconds |

## Note: Exceeding these limits may cause permanent damage.

## Device Installation Procedures

The following guidelines should be observed to avoid damaging GaAs Flip-Chips.

## Cleanliness

These devices should be handled in a clean environment.
Do Not attempt to Clean Die After installation.

## Static Sensitivity

Gallium arsenide PIN diodes are ESD sensitive and can be damaged by static electricity. Proper ESD techniques should be used when handling these devices. These devices are rated Class 0, ( $0-199 \mathrm{~V}$ ) per HBM MIL-STD-883, method 3015.7
[C $=100 \mathrm{pF} \pm 10 \%, \mathrm{R}=1.5 \mathrm{~kW} \pm 1 \%$ ]. Even though tested die pass 50 V ESD, they must be handled in a static-free environment.

## General Handling

These devices have a polymer layer which provides scratch protection for the junction area and the anode air bridge. Die can be handled with plastic tweezers or picked and placed with a \#27 tip vacuum pencil.

## Assembly Requirements using Electrically Conductive Ag Epoxy and Solder

These chips are designed to be inserted onto hard or soft substrates with the junction side down. They should be mounted onto silkscreened circuits using Electrically Conductive Ag Epoxy, approximately 1-2 mils in thickness and cured at approximately $90^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$ per manufacturer's schedule. For extended cure times $>30$ minutes, temperatures must be below $200^{\circ} \mathrm{C}$.

Sn Rich Solders are not recommended due to the Tungsten Metallization scheme beneath the gold contacts. Indalloy or $80 \mathrm{Au} / 20 \mathrm{Sn}$ Solders are acceptable. Maximum soldering temperature must be $<300^{\circ} \mathrm{C}$ for $<10$ sec.

## AIGaAs Flip-Chip PIN Diodes

## Ordering Information

| Part Number | Packaging |
| :---: | :---: |
| MA4AGCP910 | Die in Carrier |
| MADP-000910-13050T | Tape/Reel |

Circuit Mounting Dimensions ( Inches )


